

Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0089			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0112			
I _D (A)	50			
Configuration	Single			

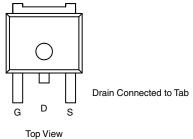
FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified
- 100 % R_g and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912

N-Channel MOSFET







ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50N10-8m9L-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C ^a	I _D	50	
	T _C = 125 °C		49	
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α
Pulsed Drain Current ^b		I _{DM}	200	
Single Pulse Avalanche Current	. 0.4	I _{AS}	43	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	92	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	D	136	W
	T _C = 125 °C	P_{D}	45	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static	1					ı	ı
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	100	-	-	.,
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	500	1
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 15 A	-	0.0071	0.0089	
Dunin Course On Chata Basistanas		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0151	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0187	Ω
		V _{GS} = 4.5 V	I _D = 10 A	-	0.0089	0.0112	
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 15 A	-	67	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2340	2950	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	1441	1810	pF
Reverse Transfer Capacitance	C _{rss}]		-	124	160	
Total Gate Charge ^c	Qg			-	46	70	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 50 \text{ A}$	-	7.5	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	10	-	
Gate Resistance	R _g		f = 1 MHz	6	12.3	18.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	18	
Rise Time ^c	t _r	V _{DD}	= 50 V, $R_1 = 1 \Omega$	-	12	18	
Turn-Off Delay Time ^c	t _{d(off)}		$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	95	145	ns
Fall Time ^c	t _f			-	120	180	1
Source-Drain Diode Ratings and Char-	acteristics ^b	•			•		
Pulsed Current ^a	I _{SM}			-	-	200	Α
Forward Voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	0.8	1.5	V

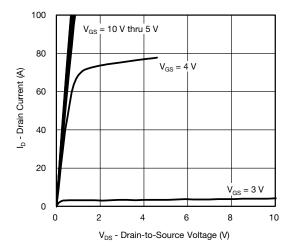
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

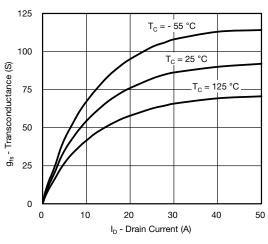
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



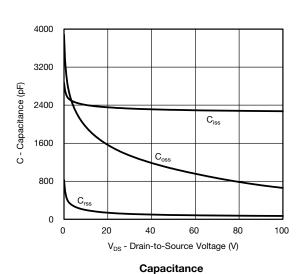
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

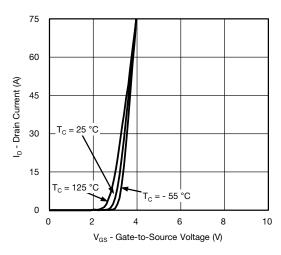


Output Characteristics

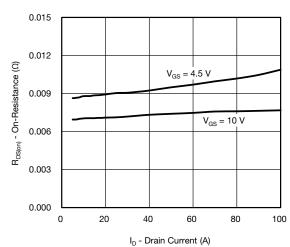


Transconductance

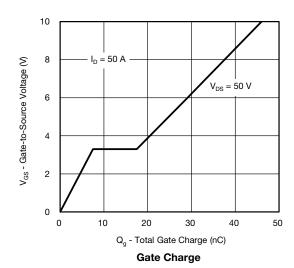




Transfer Characteristics

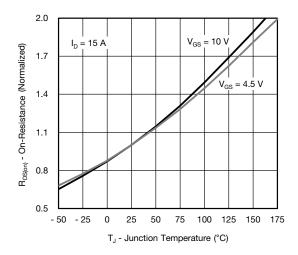


On-Resistance vs. Drain Current

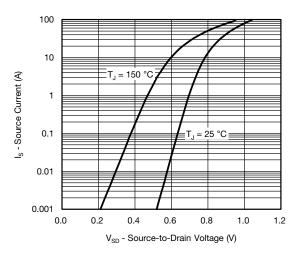




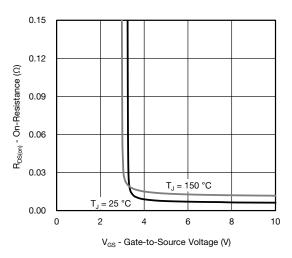
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



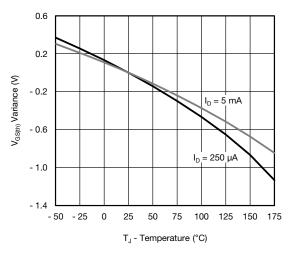
On-Resistance vs. Junction Temperature



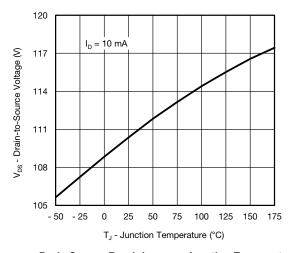
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



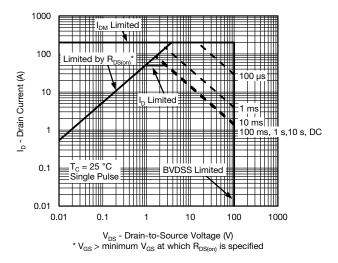
Threshold Voltage



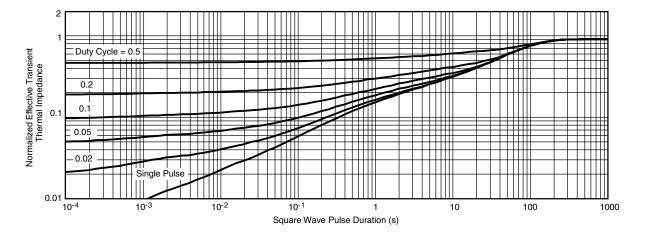
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



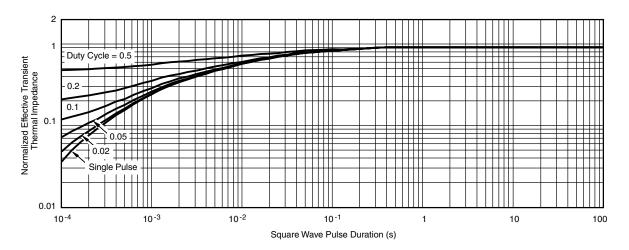
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

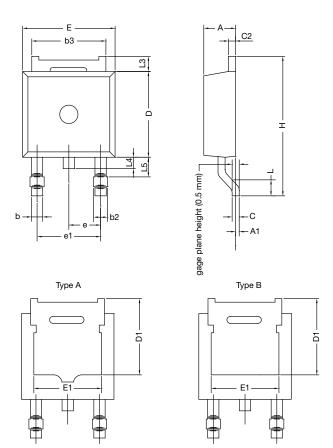
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262778.



TO-252AA Case Outline



DIM	MILLIN	METERS	INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28	BSC	0.090	BSC
e1	4.56	4.56 BSC		BSC
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

ECN: T25-0122-Rev. C, 12-May-2025 DWG: 6019

Notes

- Dimension L3 is for reference only
- Dimension D1 and E1 on type A and B is the same



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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